



8/8/01

Docket No: 0756-2330

IN THE U.S. PATENT AND TRADEMARK OFFICE

IN RE PATENT APPLICATION OF: ) Art Unit: 2823  
Shunpei YAMAZAKI et al ) Ex.: B. Kebede  
SERIAL NO. 09/894,125 )  
FILED: 06/29/2001 )  
FOR: CRYSTALLINE SEMICONDUCTOR )  
THIN FILM, METHOD OF )  
FABRICATING THE SAME, )  
SEMICONDUCTOR DEVICE AND )  
METHOD OF FABRICATING THE SAME)

TC 2823-A  
JUL 12 2001  
U.S. PATENT & TRADEMARK OFFICE

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents  
U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

Please preliminarily amend the above identified patent application as follows:

In the Claims:

Please add the following new claims 19-26:

*A*  
19. (New) A method of manufacturing a semiconductor device comprising the steps of:  
*CY*  
    forming a semiconductor film comprising silicon over a substrate;  
    irradiating said semiconductor film with laser light in an atmosphere containing oxygen for crystallizing said semiconductor film;  
    removing an oxide film from a surface of the semiconductor film by etching after the irradiation of the laser light; and